

OFFSET VERTICAL DEVICE

ABSTRACT OF THE DISCLOSURE

The present invention includes a method for forming a memory array and the memory array produced therefrom. Specifically, the memory array includes at least one first-type memory device, each of the at least one first-type memory device comprising a first transistor and a first underlying capacitor that are in electrical contact to each other through a first buried strap, where the first buried strap positioned on a first collar region; and at least one second-type memory cell, where each of the at least one second-type memory device comprises a second transistor and a second underlying capacitor that are in electrical contact through an offset buried strap, where the offset buried strap is positioned on a second collar region, wherein the second collar region has a length equal to the first collar region.